

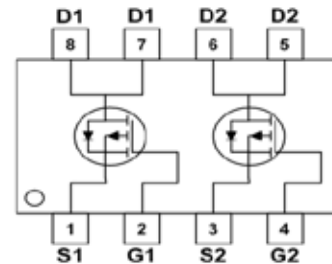
P-Channel Enhancement Mode Power MOSFET

Description

The RM6A5P30S8 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

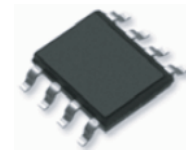
- $V_{DS} = -30V, I_D = -6.5A$
- $R_{DS(ON)} < 42m\Omega @ V_{GS} = -4.5V$
- $R_{DS(ON)} < 25m\Omega @ V_{GS} = -10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface mount package



Schematic diagram and pin assignment

Application

- PWM applications
- Load switch
- Power management
- Halogen-free
- P/N suffix V means AEC-Q101 qualified, e.g:RM6A5P30S8V



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
6A5P30	RM6A5P30S8	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-6.5	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	-26	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	85	$^\circ\text{C/W}$
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-6A$	-	-	25	m Ω
		$V_{GS}=-4.5V, I_D=-4A$	-	-	42	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-6A$	17	-	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{ISS}	$V_{DS}=-15V, V_{GS}=0V,$ $F=1.0MHz$	-	1345	-	PF
Output Capacitance	C_{OSS}		-	194	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	158	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-6A,$ $V_{GS}=-10V, R_{GEN}=3.3\Omega$	-	4.6	-	nS
Turn-on Rise Time	t_r		-	14.8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	41	-	nS
Turn-Off Fall Time	t_f		-	19.6	-	nS
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-6A, V_{GS}=-4.5V$	-	12.6	-	nC
Gate-Source Charge	Q_{gs}		-	4.8	-	nC
Gate-Drain Charge	Q_{gd}		-	4.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1A$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

RATING AND CHARACTERISTICS CURVES (RM6A5P30S8)

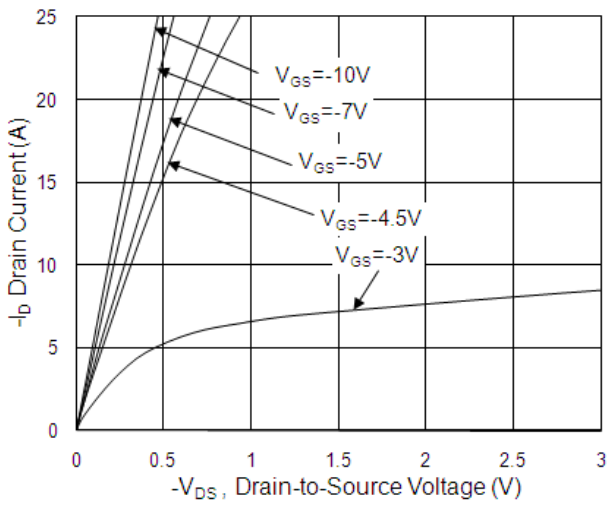


Fig.1 Typical Output Characteristics

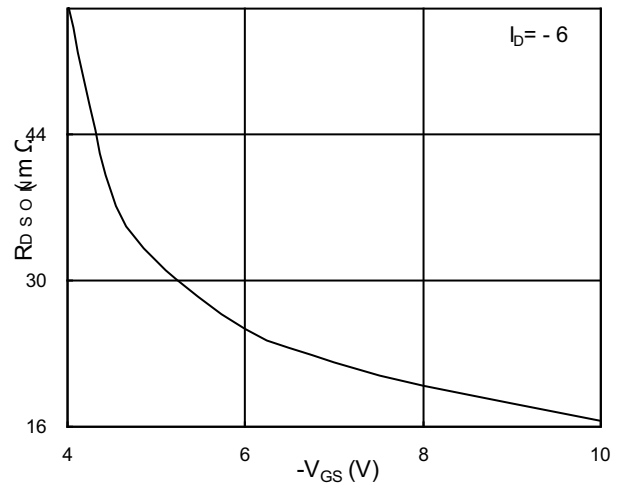


Fig.2 On-Resistance v.s Gate-Source

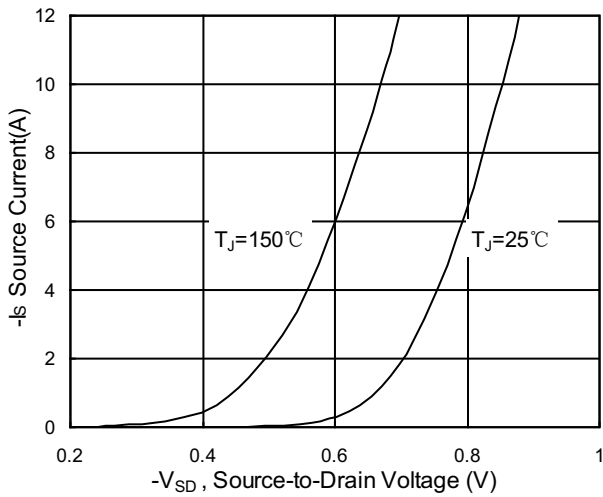


Fig.3 Forward Characteristics of Reverse

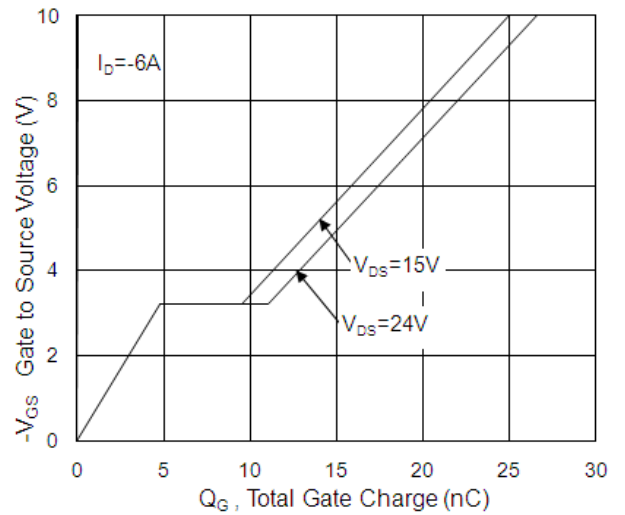


Fig.4 Gate-Charge Characteristics

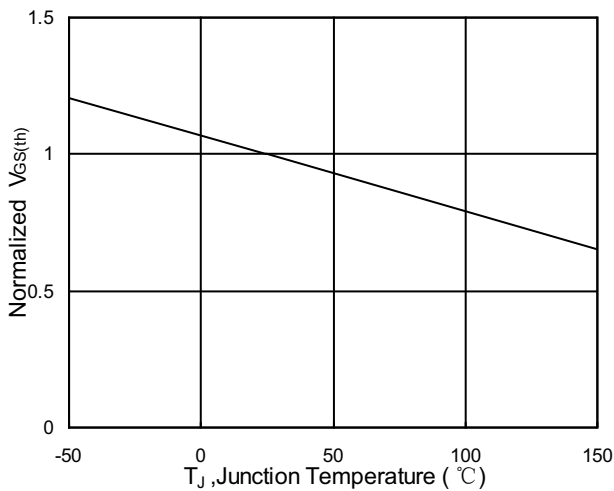


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

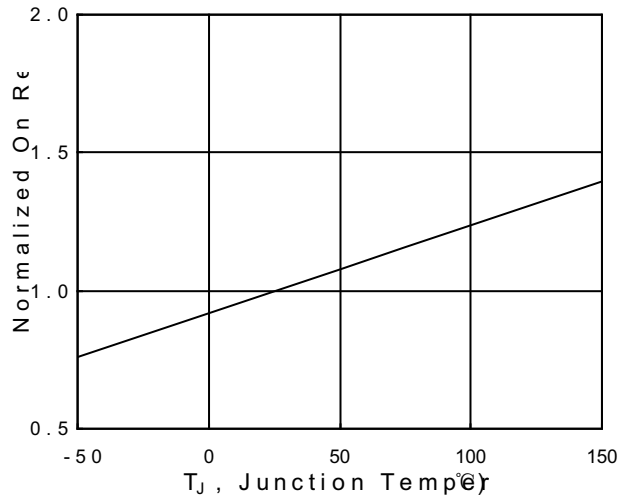


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

RATING AND CHARACTERISTICS CURVES (RM6A5P30S8)

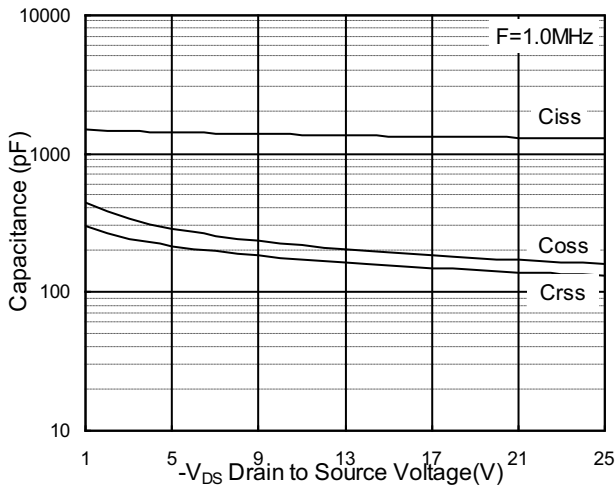


Fig.7 Capacitance

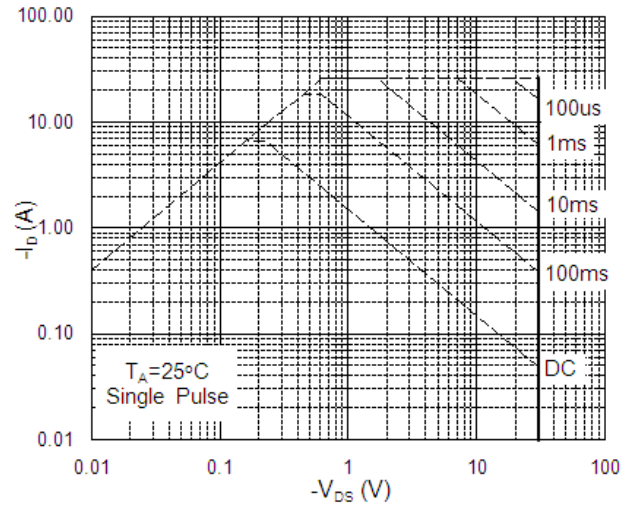


Fig.8 Safe Operating Area

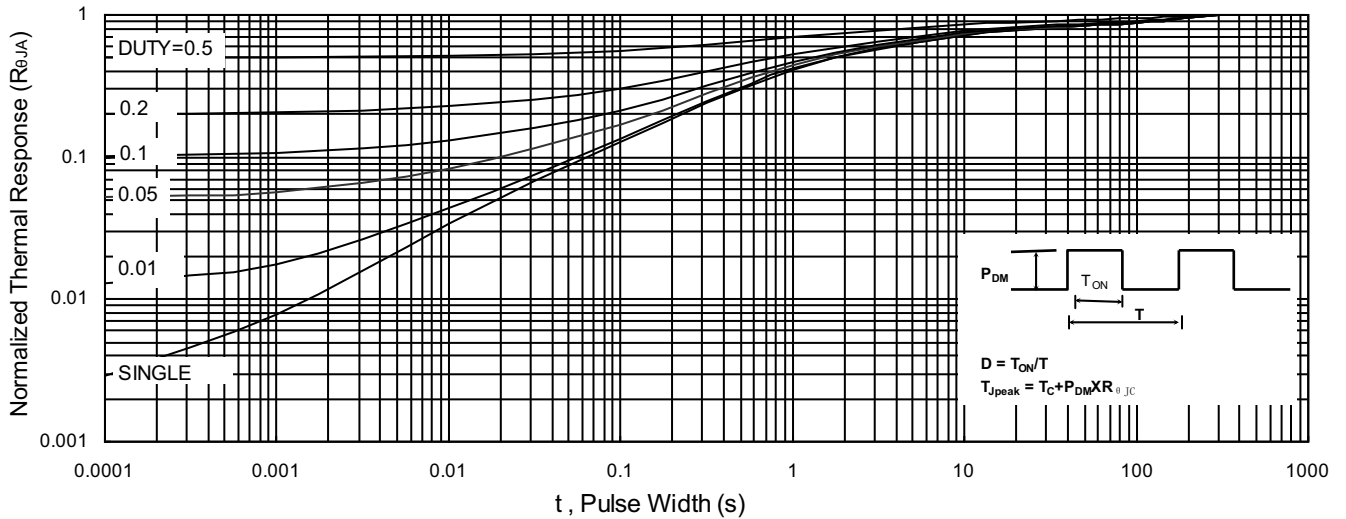


Fig.9 Normalized Maximum Transient Thermal Impedance

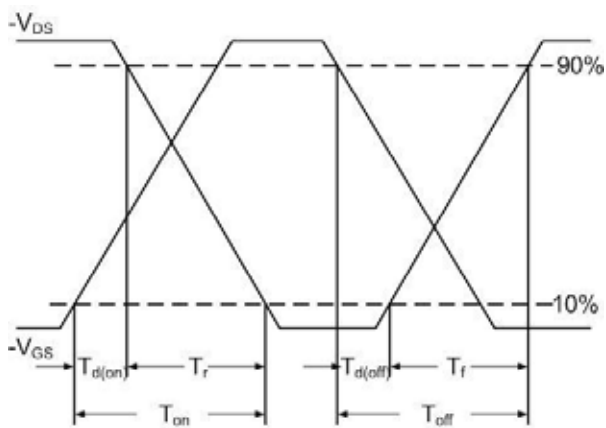


Fig.10 Switching Time Waveform

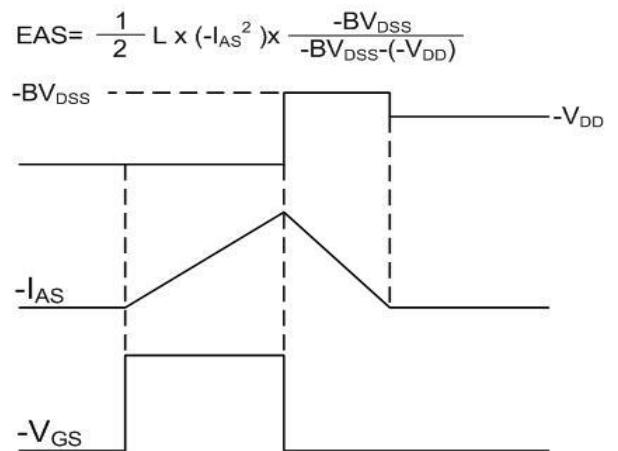
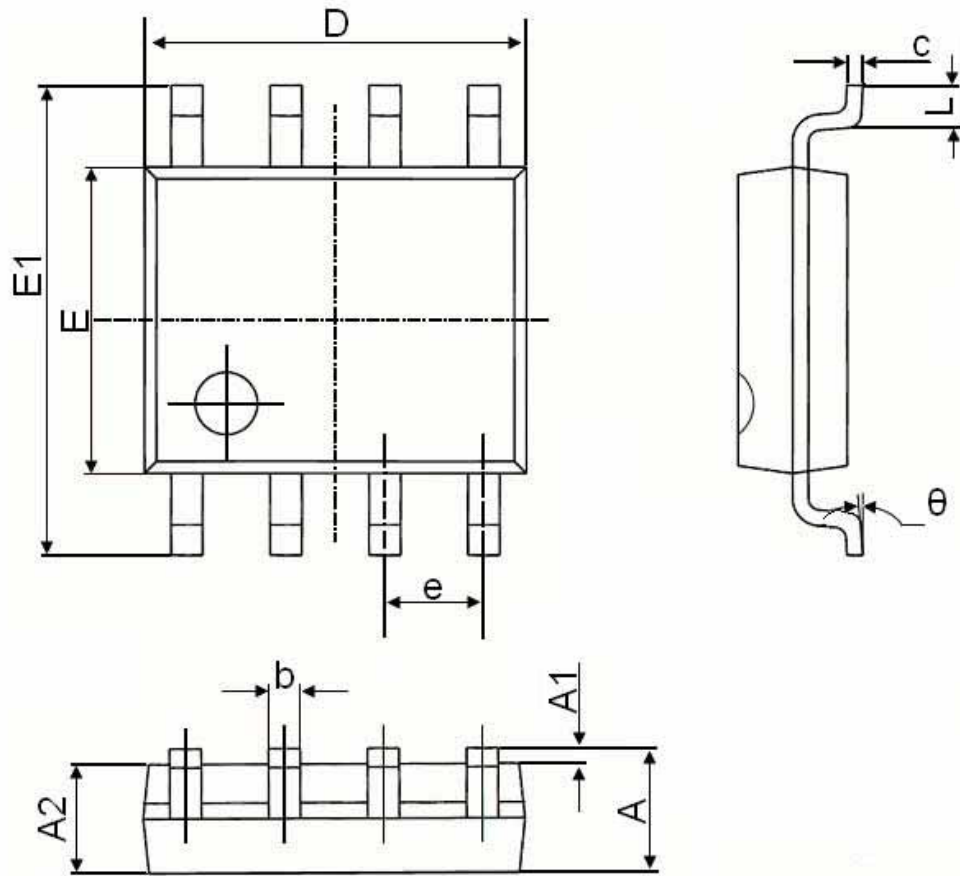


Fig.11 Unclamped Inductive Switching Waveform

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°

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